

ASG1210**表面贴装 超高频高压二极管**

反向电压：10 kV；正向电流：100 mA；反向恢复时间：75 ns

Surface Mount Super-Fast Recovery High Voltage Diode

Reverse Voltage: 10 kV

Average Forward Current: 100 mA

Maximum Reverse Recovery Time: 75 ns

技术资料**Technical Data**

- 产品级别：外贸级
- 封装形式：环氧封装
- 引线：表面贴装内弯式
- 极性：色带指示负极
- Product Grade: International Standard
- Package Type: Epoxy Encapsulation
- Lead: Inside Bend
- Polarity: Cathode Indicated by Color Band

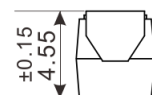
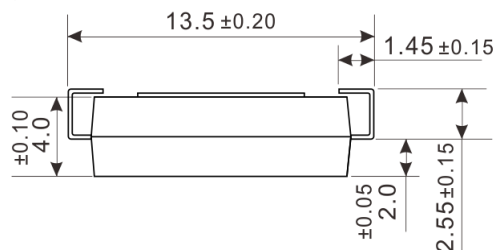
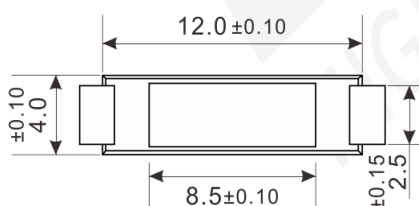
**产品标准****Product Standard**

Q/FT TRV0003-2022 《高压二极管》

外形尺寸**External Dimensions**

封装代号：HVS-412E

Package Code: HVS-412E

**HVS-412E**

单位：mm

验收标准

Acceptance Criteria

GB/T 4023 《半导体器件分立器件和集成电路 第2部分：整流二极管》

Semiconductor Devices-Discrete Devices and Integrated Circuits-Part 2: Rectifier Diode.

特性及参数值

Characteristics and Parameter

除非另有规定，环境温度均为 25℃。

The ambient temperature is 25℃ unless otherwise specified.

电气特性 Electrical Characteristics	符 号 Symbol	额定值 Ratings	单 位 Unit
最大反向重复峰值电压 Maximum Repetitive Peak Reverse Voltage	V_{RRM}	10	kV
最大反向不重复峰值电压 Maximum Non-repetitive Peak Reverse Voltage	V_{RSM}	11	kV
最大正向平均电流 Maximum Average Forward Current (@ $T_{oil} = 55^{\circ}C$)	$I_{F(AV)}$	100	mA
最大正向浪涌电流 Maximum Surge Current	I_{FSM}	10	A
最大正向峰值电压 Maximum Peak Forward Voltage (@ $I_F = I_{F(AV)}$)	V_{FM}	≤ 14	V
最大直流反向电流 Maximum DC Reverse Current (@ $V_R = V_{RRM}$)	I_R	≤ 2 ($T_{oil} = 25^{\circ}C$)	μA
		≤ 10 ($T_{oil} = 100^{\circ}C$)	
最大反向恢复时间 Maximum Reverse Recovery Time ($I_F = 100mA$, $I_R = 200mA$)	t_{rr}	≤ 75	ns
有效工作结温 Operating Junction Temperature Range	T_J	$-55 \sim +125$	$^{\circ}C$
贮存温度 Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^{\circ}C$